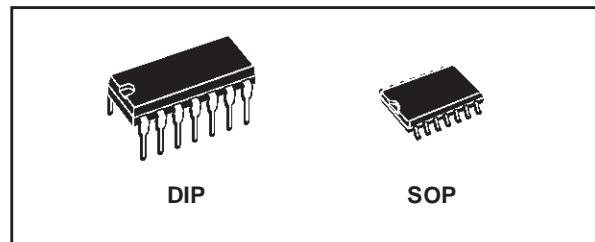




HCF4066B

QUAD BILATERAL SWITCH FOR TRANSMISSION OR MULTIPLEXING OF ANALOG OR DIGITAL SIGNALS

- 15V DIGITAL OR $\pm 7.5V$ PEAK TO PEAK SWITCHING
- 125 Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- SWITCH ON RESISTANCE MATCHED TO WITHIN 5 Ω TYP. OVER 15V SIGNAL INPUT RANGE
- ON RESISTANCE FLAT OVER FULL PEAK TO PEAK SIGNAL RANGE
- HIGH ON/OFF OUTPUT VOLTAGE RATIO : 65dB TYP. at $f_{IS} = 10KHz$, $R_L = 10K\Omega$
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at $f_{IS} = 1KHz$, $V_{IS} = 5 V_{pp}$, $V_{DD} - V_{SS} \geq 10V$, $R_L = 10K\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE : 10pA TYP. at $V_{DD} - V_{SS} = 10V$, $T_{amb} = 25^\circ C$
- EXTREMELY HIGH CONTROL INPUT IMPEDANCE (control circuit isolated from signal circuit $10^{12}\Omega$ typ.)
- LOW CROSSTALK BETWEEN SWITCHES : 50dB Typ. at $f_{IS} = 0.9MHz$, $R_L = 1K\Omega$
- MATCHED CONTROL - INPUT TO SIGNAL OUTPUT CAPACITANCE : REDUCES OUTPUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE SWITCH ON : 40MHz (Typ.)
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS



ORDER CODES

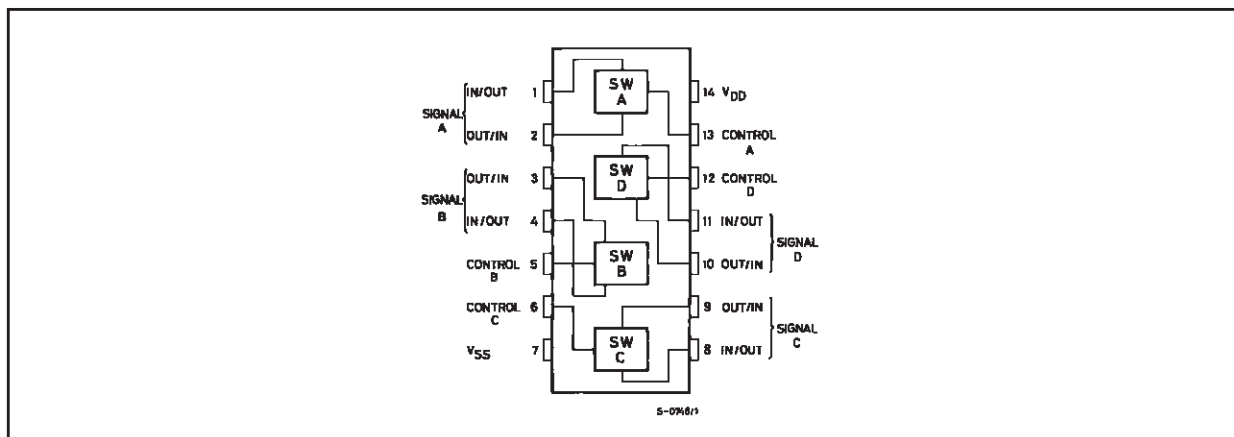
PACKAGE	TUBE	T & R
DIP	HCF4066BEY	
SOP	HCF4066BM1	HCF4066M013TR

- INPUT LEAKAGE CURRENT
 $I_I = 100nA$ (MAX) AT $V_{DD} = 18V$ $T_A = 25^\circ C$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4066B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4066B is a QUAD BILATERAL SWITCH intended for the transmission or multiplexing of analog or digital signals. It is pin for pin compatible with HCF4016B, but exhibits a much lower ON resistance. In addition,

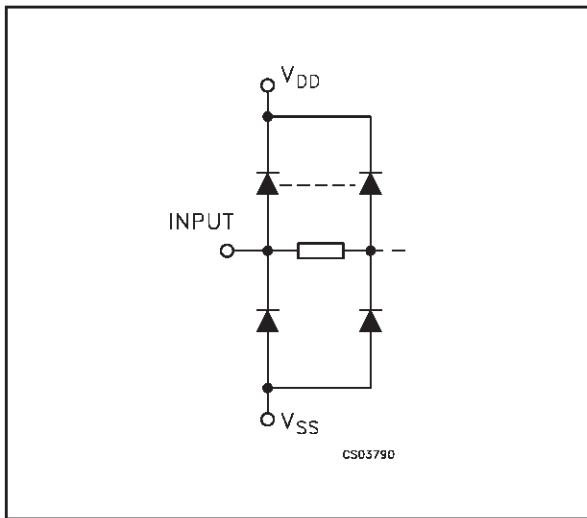
PIN CONNECTION



the ON resistance is relatively constant over the full input signal range. The HCF4066B consists of four independent bilateral switches. A single control signal is required per switch. Both the p and n device in a given switch are biased ON or OFF simultaneously by the control signal. As shown in schematic diagram, the well of the n-channel device on each switch is either tied to the input when the switch is ON or to V_{SS} when the switch is OFF. This configuration eliminates

the variation of the switch-transistor threshold voltage with input signal, and thus keeps the ON resistance low over the full operating signal range. The advantages over single channel switches include peak input signal voltage swings equal to the full supply voltage, and more constant ON impedance over the input signal range. For sample and hold applications, however, the HCF4016B is recommended.

INPUT EQUIVALENT CIRCUIT



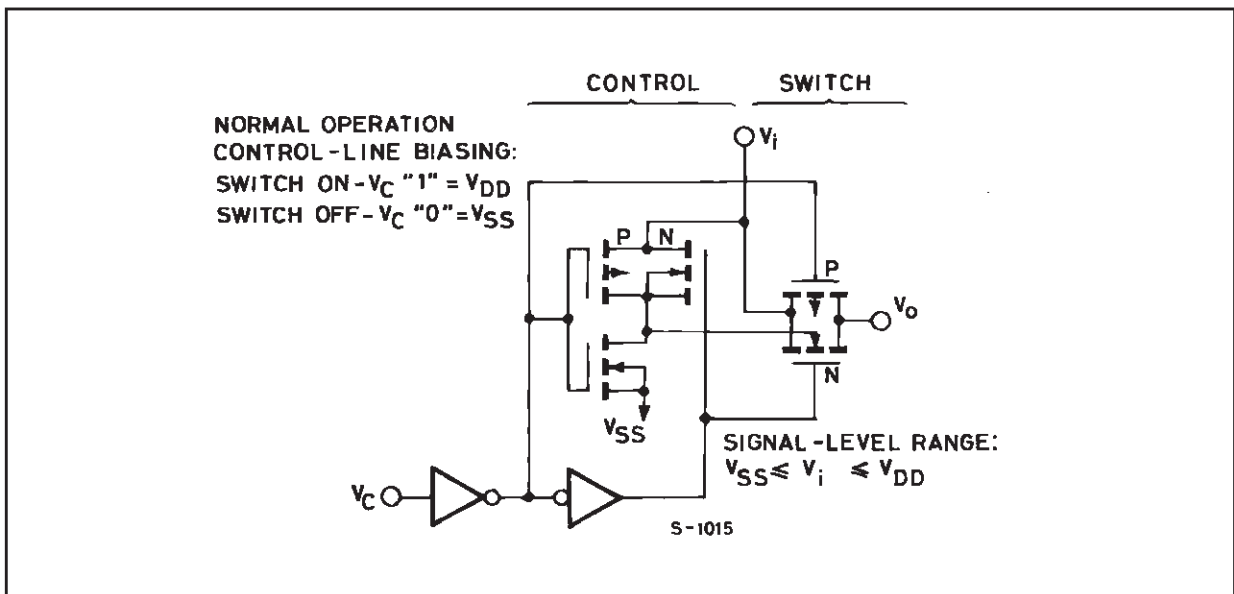
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 8, 11	A to D I/O	Independent Inputs/Outputs
2, 3, 9, 10	A to D O/I	Independent Outputs/Inputs
13, 5, 6, 12	CONTROL A to D	Enable Inputs
7	V_{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

SCHEMATIC DIAGRAM (1 OF 4 IDENTICAL SWITCHES AND ITS ASSOCIATED CONTROL CIRCUITY)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	$^{\circ}\text{C}$

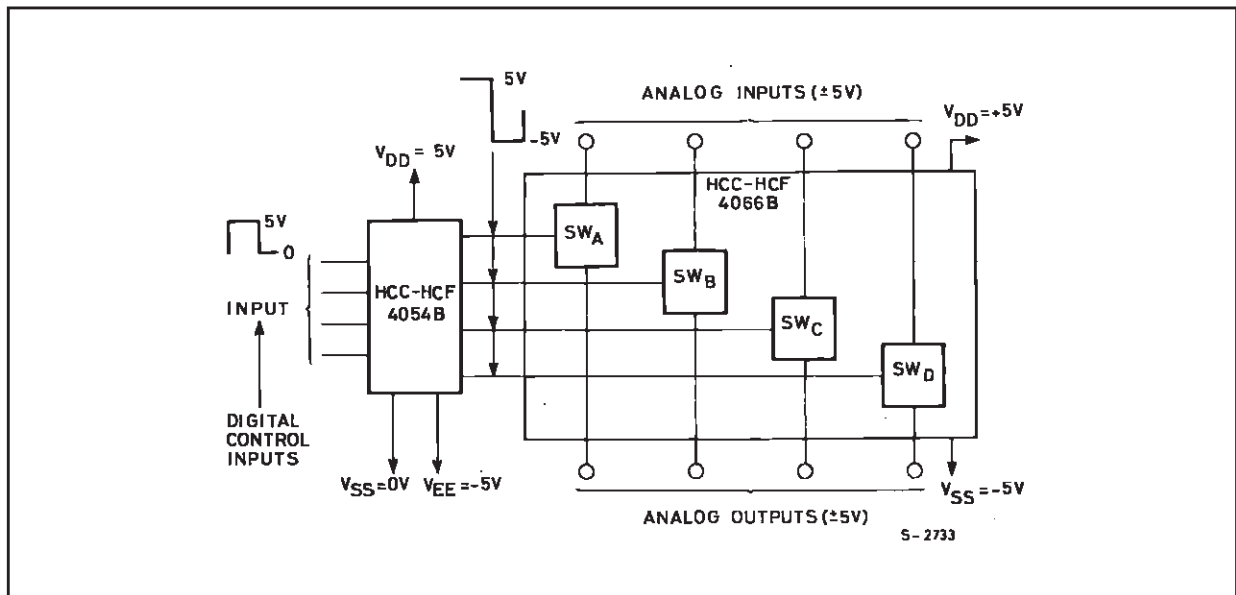
ELECTRICAL CHARACTERISTICS

($T_{amb} = 25^{\circ}\text{C}$, Typical temperature coefficient for all V_{DD} value is 0.3 %/ $^{\circ}\text{C}$)

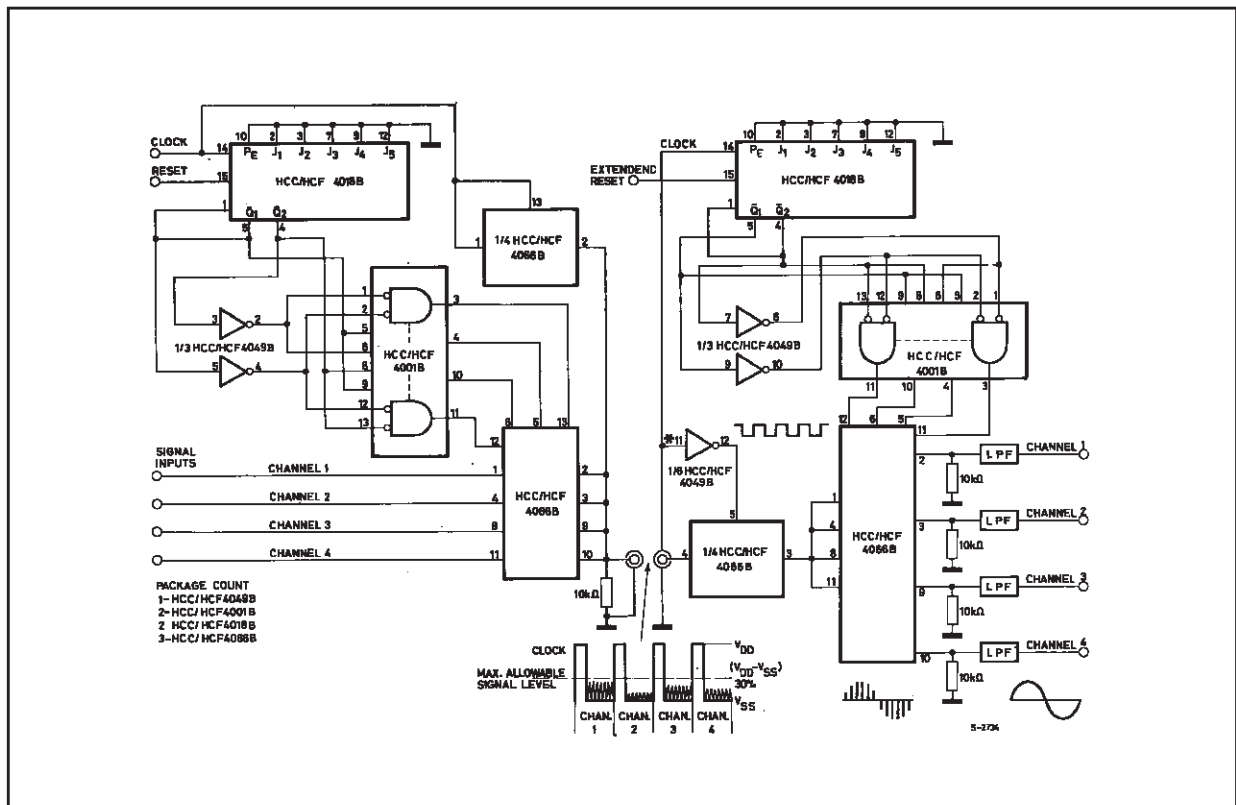
Symbol	Parameter	Test Condition			Value						Unit	
			V_I (V)	V_{DD} (V)	$T_A = 25^{\circ}\text{C}$			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
I_L	Quiescent Device Current (all switches ON or all switches OFF)		0/5	5		0.01	0.25		7.5		7.5	μA
			0/10	10		0.01	0.5		15		15	
			0/15	15		0.01	1		30		30	
			0/20	20		0.02	5		150		150	
SIGNAL INPUTS (V_{IS}) and OUTPUTS (V_{OS})												
R_{ON}	Resistance	$V_C = V_{DD}$, $R_L = 10\text{K}\Omega$ Return to $(V_{DD} - V_{SS})/2$ $V_{IS} = V_{SS}$ to V_{DD}	5		470	1050		1200		1200	Ω	
			10		180	400		500		500		
			15		125	240		300		300		
Δ_{ON}	Resistance Δ_{RON} (between any 2 of 4 switches)	$R_L = 10\text{K}\Omega$, $V_C = V_{DD}$	5		5						Ω	
			10		10							
			15		15							
TDH	Total Harmonic Distortion	$V_C = V_{DD} = 5\text{V}$, $V_{SS} = -5\text{V}$ V_{IS} (p-p) = 5V, $R_L = 10\text{K}\Omega$ (sine wave centered in 0V) $f_{IS} = 1\text{KHz}$ sine wave			0.4						%	
	-3dB Cutoff Frequency (Switch on)	$V_C = V_{DD} = 5\text{V}$, $V_{SS} = -5\text{V}$ V_{IS} (p-p) = 5V, $R_L = 1\text{K}\Omega$ (sine wave centered in 0V)			40						MHz	
	-50dB Feedthrough Frequency (switch off)	$V_C = V_{SS} = -5\text{V}$ V_{IS} (p-p) = 5V, $R_L = 1\text{K}\Omega$ (sine wave centered in 0V)			1						MHz	

Symbol	Parameter	Test Condition			Value						Unit		
			V _I (V)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C			
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
	-50dB Crosstalk Frequency	V _{C(A)} = V _{DD} = +5V V _{C(B)} = V _{SS} = -5V V _{IS(A)} = 5V (p-p) 50Ω source, R _L = 1KΩ				8						MHz	
t _{pd}	Propagation Delay Time (signal input to output)	R _L = 200KΩ, V _C = V _{DD} V _{SS} = GND, C _L = 50pF V _{IS} = 10V square wave centered on 5V t _r , t _f = 20ns				20	40					ns	
						10	20						
						7	15						
C _{IS}	Input Capacitance	V _C = V _{SS} = -5		+5		8						pF	
C _{OS}	Output Capacitance					8							
C _{IOS}	Feedthrough					0.5							
	Input/Output Leakage Current Switch OFF	V _C = 0V V _{IS} = 18V, V _{OS} = 0V V _{IS} = 0V, V _{OS} = 18V		18		±10 ⁻³	±0.1		±1		±1	μA	
CONTROL (V_C)													
V _{ILC}	Control Input Low Voltage	I _{IS} < 10 μA V _{IS} = V _{SS} , V _{OS} = V _{DD} and V _{IS} = V _{DD} , V _{OS} = V _{SS}		5				1		1		1	V
				10				2		2		2	
				15				2		2		2	
V _{IHC}	Control Input High Voltage	V _{IS} = V _{DD} , V _{OS} = V _{SS}		5	3.5			3.5		3.5			V
				10	7			7		7			
				15	11			11		11			
I _I	Input Leakage Current	V _{IS} ≤ V _{DD} V _{DD} - V _{SS} = 18V		18		±10 ⁻⁵	±0.1		±1		±1	μA	
	Crosstalk (control input to signal output)	V _C = 10V (sq. wave) t _r , t _f = 20ns R _L = 10KΩ		10		50						mV	
	Turn - On Propagation Delay Time	V _{IN} = V _{DD} , t _r , t _f = 20ns C _L = 50pF, R _L = 1KΩ		5		35	70						ns
				10		20	40						
				15		15	30						
	Control Input Repetition Rate	V _{IS} =V _{DD} , V _{SS} =GND R _L = 1KΩ to GND C _L = 50pF, V _C = 10V sq. wave center on 5V t _r , t _f = 20ns V _{OS} =1/2V _{OS} at 1KHz		5		6							MHz
				10		9							
				15		9.5							
C _I	Input Capacitance	Any Input				5	7.5					pF	

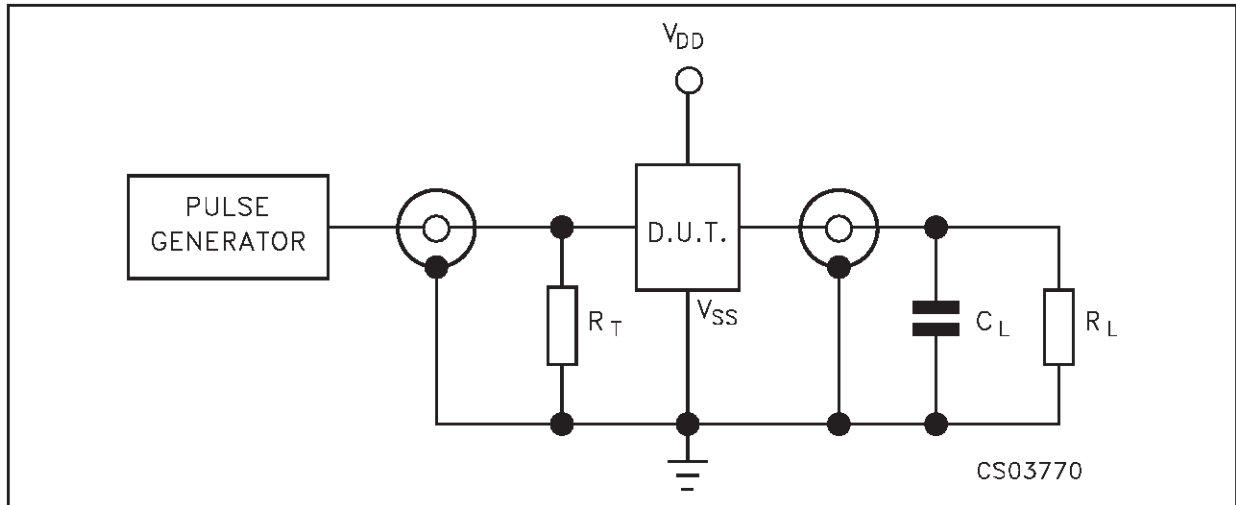
TYPICAL APPLICATIONS (BIDIRECTIONAL SIGNAL TRANSMISSION VIA DIGITAL CONTROL LOGIC)



TYPICAL APPLICATIONS (4-CHANNEL PAM MULTIPLEXER SYSTEM DIAGRAM)

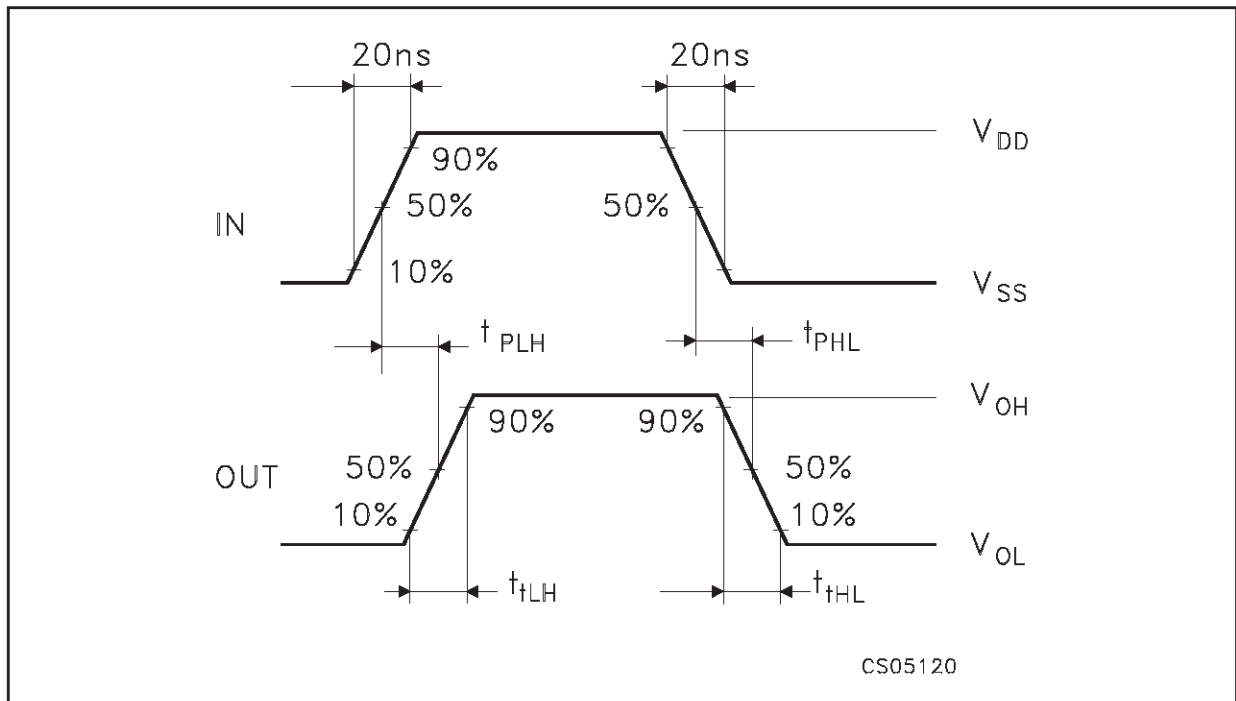


TEST CIRCUIT



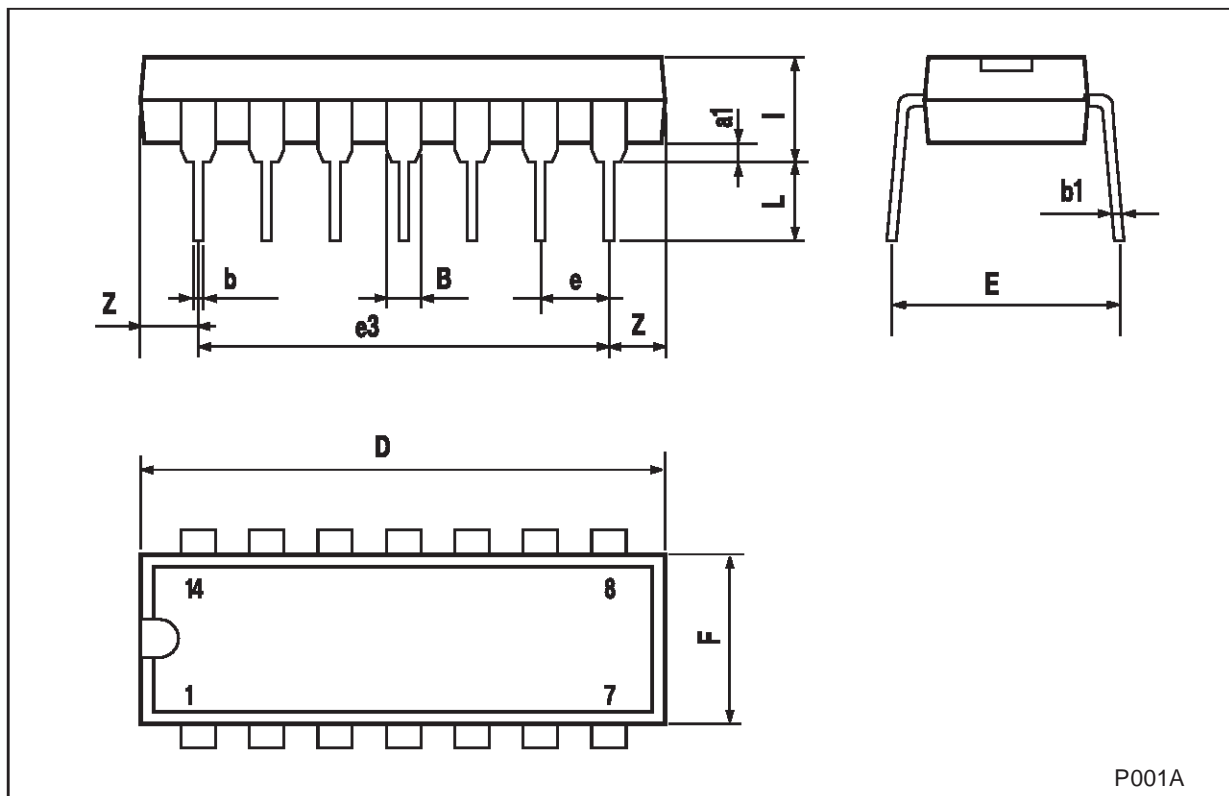
$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_L = 200\text{K}\Omega$
 $R_T = Z_{\text{OUT}}$ of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)



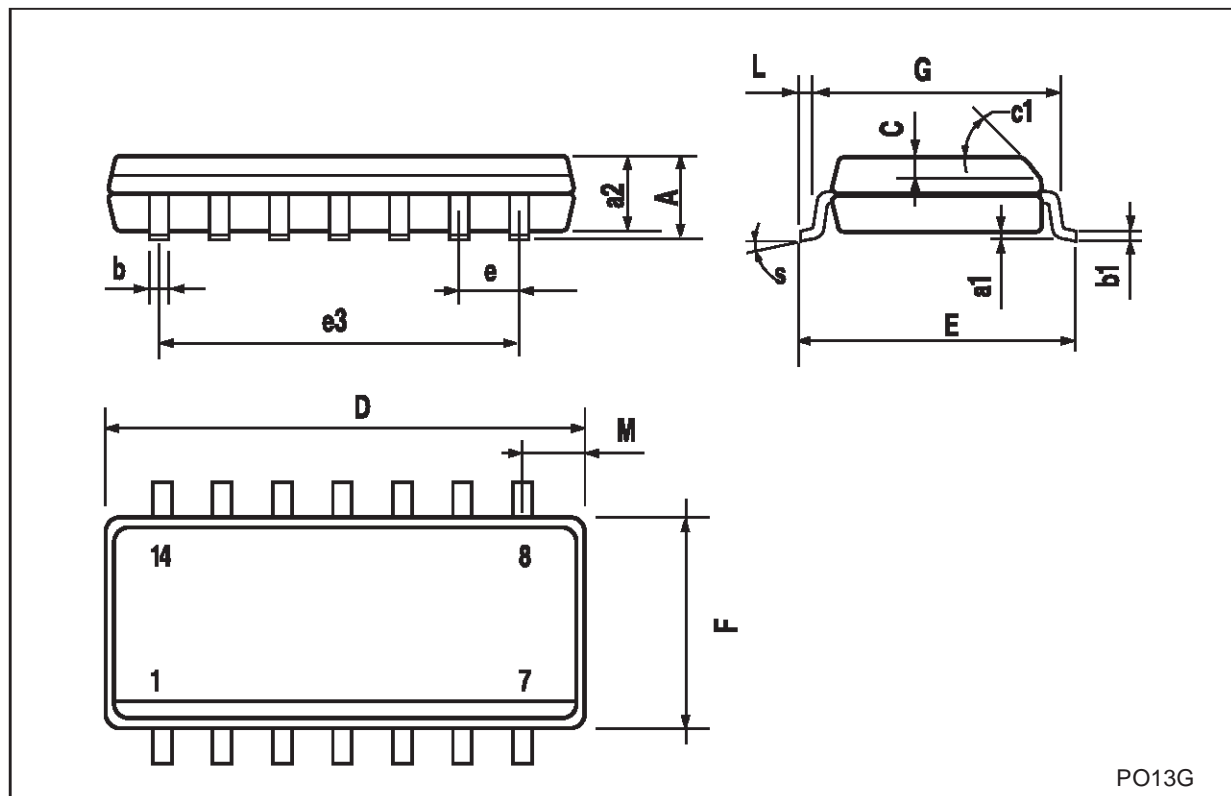
Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom

© <http://www.st.com>



This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.